

Appl. No.
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Sub 23
B3
11. (Amended) A process of forming electrically isolated integrated devices in a silicon substrate, comprising:

masking portions of the substrate to define unmasked field isolation regions;

growing field oxide in the field isolation regions by [dry] hydrogen-free oxidation alone at an oxidant partial pressure **[of greater than about]** between about 5 atm and 30 atm and a temperature of greater than about 900°C; and

forming electrical devices between the field isolation regions.

Sub 24
B4
14. (Amended) A process of forming an integrated circuit on a semiconductor substrate, comprising:

masking portions of the substrate with a mask comprising silicon nitride;

growing a field oxide by [dry] hydrogen-free oxidation alone to a thickness sufficient for electrical isolation of devices within the substrate without forming silicon nitride inclusions therein;

removing the mask after growing the field oxide; and

forming a gate oxide of uniform thickness adjacent the field oxide on the semiconductor substrate without performing a prior sacrificial oxidation.

NOT AMENDED
16. The process of Claim 15, wherein growing the field oxide further comprises maintaining the oxidant partial pressure at about 5-30 atm.

17. The process of Claim 15, wherein growing the field oxide further comprises maintaining the substrate at greater than about 900°C.

Remarks:

Applicants appreciate the courtesies extended by Examiner Fourson during the personal interview conducted by Applicants' counsel, James Bear, on September 17, 1999. During that interview, the amendments made herein were discussed, and the phrase "hydrogen free" was suggested by Examiner Fourson to remove any ambiguity with regard to the meaning of "dry etch". It is understood that the claims, as presently amended, are in a condition for allowance, and the arguments which follow reflect the discussions with the Examiner.